(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
18 May 2006 (18.05.2006)

PCT

(10) International Publication Number
WO 2006/052379 A1

(51) International Patent Classification:
H01L 29/786 (2006.01) *H01L 21/336* (2006.01)

(21) International Application Number:
PCT/US2005/036894

(22) International Filing Date: 12 October 2005 (12.10.2005)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/986,399 10 November 2004 (10.11.2004) US

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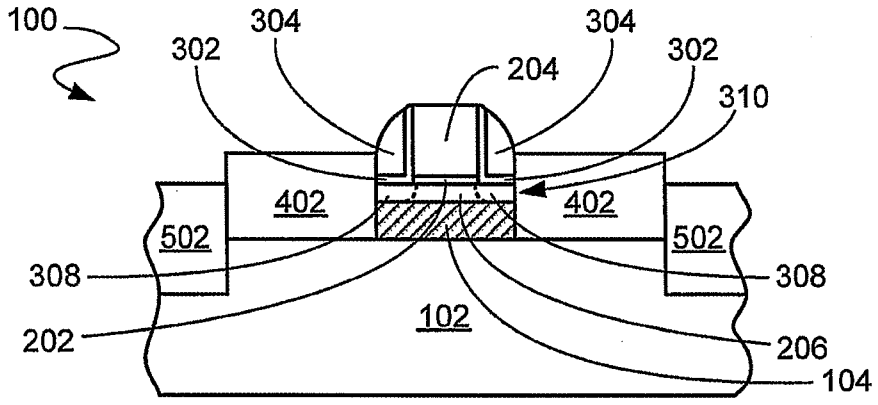
(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, LY, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: STRAINED FULLY DEPLETED SILICON ON INSULATOR SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREFOR



(57) Abstract: A semiconductor substrate (102) is provided having an insulator (104) thereon with a semiconductor layer (106) on the insulator (104). A deep trench isolation (108) is formed, introducing strain to the semiconductor layer (106). A gate dielectric (202) and a gate (204) are formed on the semiconductor layer (106). A spacer (304) is formed around the gate (204), and the semiconductor layer (106) and the insulator (104) are removed outside the spacer (304). Recessed source/drain (402) are formed outside the spacer (304).

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